

REMARKS/ARGUMENTS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

Claims 1-6, 8-17, 20-25, 27-35, and 38 and 40 are presently active in this case, Claims 1, 8, 12, and 30 having been amended and Claims 7, 26 and 39 having been canceled by the present amendment, Claims 18-19, 36-37 and 41-87 having previously been canceled.

In the outstanding Official Action, Claims 12 and 30 were objected to as being a substantial duplicate of Claims 11 and 29, respectively. Claims 1-4, 9-10, 13-14, 20-23, 27-28 and 31-32 were rejected under 35 USC §102(e) as anticipated by Lee et al. (US 6,662,223); Claims 1-6, 9-10, 13-17, 20-25, 27, 28, 31-35 and 38-40 were rejected under 35 USC §102(b) as anticipated by Sakui et al. (US 6,307,807); Claims 11, 112, 29 and 30 were rejected under 35 USC §103 as being unpatentable over Lee et al. or Sakui et al. in view of Hemink et al. (US 5,949,714); and Claims 7, 8 and 26 were objected to as being dependent upon a rejected bas claim, but were otherwise indicated as including allowable subject matter if rewritten in independent form.

Applicants acknowledge with appreciation the indication that Claims 7, 8 and 26 include allowable subject matter. In light of this indication, and to expedite issuance of a patent from the present application, Claims 1 and 20 have been amended to include the features stated in Claims 7 and 26, and Claims 7 and 26 have been canceled

In response to the objection to Claims 12 and 30, these claims have been amended to overcome the objection thereto without the addition of new matter.

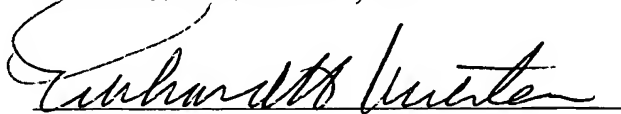
Further, Claim 38 has been amended to clarify the claimed invention consistent with Applicants' FIG. 33 disclosure. Claim 40 has been amended to clarify the claimed invention consistent with Applicants' FIG. 37 disclosure. No new matter has been added.

In addition, in regard to the terminology "high withstand pressure transistor" used in the original specification and claims, this terminology has been clarified to --high voltage potential transistor -- since Applicants consider that the original reference to "high withstand pressure transistor" is non-idiomatic. Applicants consider that the technical meaning of the high voltage transistor is the same as that of the high withstand pressure transistor, and that the present amendment therefore does not add new matter.

Consequently, in view of the present amendment and in light of the above comments, the present application is believed to be in condition for allowance. An early and favorable action to that effect is respectfully requested.

Respectfully submitted,

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